

Silicon NPN Power Transistor

2SC3729

DESCRIPTION

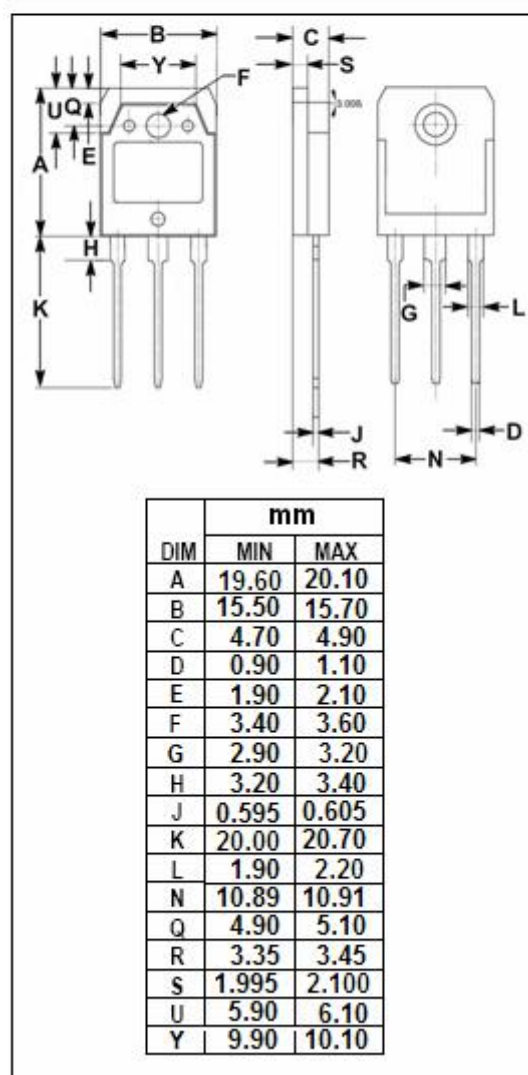
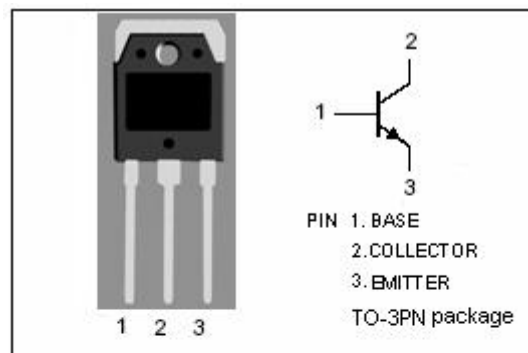
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 800V(\text{Min})$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	16	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}; R_{BE} = \infty$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown voltage	$I_E = 10\text{mA}; I_C = 0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 1.25\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 5\text{A}; I_B = 1.25\text{A}$			1.5	V
I_{CES}	Collector Cutoff Current	$V_{CE} = 1500\text{V}; R_{BE} = 0$			0.5	mA
h_{FE}	DC Current Gain	$I_C = 1\text{A}; V_{CE} = 5\text{V}$	8			